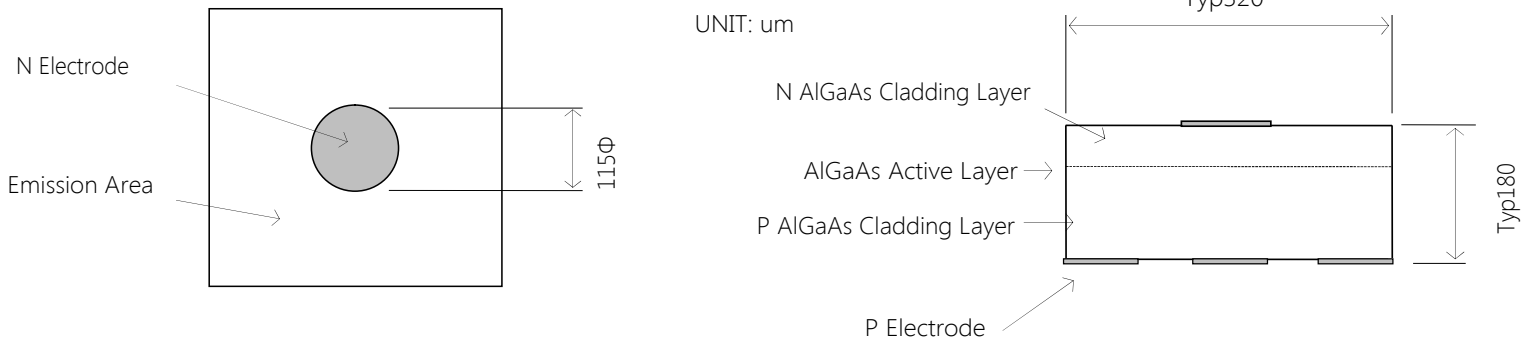


Radiation	Type	Electrodes
Infrared	AlGaAs	N (cathode) up



### Physical Characteristics & Structure

Material: AlGaAs  
 Bond Pad Size: 115 $\mu\text{m}$  diameter  
 Junction Size: 320 $\mu\text{m}$  x 320 $\mu\text{m}$   
 Anode Metalization: Gold Alloy  
 Thickness: 180 $\mu\text{m}$   
 Cathode Metalization: Gold Alloy

### Electrical & Optical Characteristics ( $T_a = 25^\circ\text{C}$ )

ITEMS	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNIT
Forward Voltage	$V_f$	$I_f=20\text{mA}$	--	--	1.6	V
Reverse Voltage	$V_r$	$I_r=10\mu\text{A}$	5	--	--	V
Radiant Power*	$\Phi_e$	$I_f=20\text{mA}$	4.0	--	--	mW
Peak Wavelength	$\lambda_p$	$I_f=20\text{mA}$	--	830	--	nm
Spectral Bandwidth at 50%	$\Delta\lambda_{0.5}$	$I_f=20\text{mA}$	--	40	--	nm

\* LED chip is mounted on TO-18 gold header without resin coated.

### Absolute Maximum Ratings ( $T_a = 25^\circ\text{C}$ )

Continuous Maximum Forward Current: 100mA (DC)  
 Reverse Voltage: 5V ( $I_R=10\mu\text{A}$ )  
 Storage Temperature  
 while on mylar membrane: 0 to 40 °C  
 after removal from mylar membrane: -30 to 100 °C



We reserve the right to make changes to improve technical design and may do so without further notice. Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer.